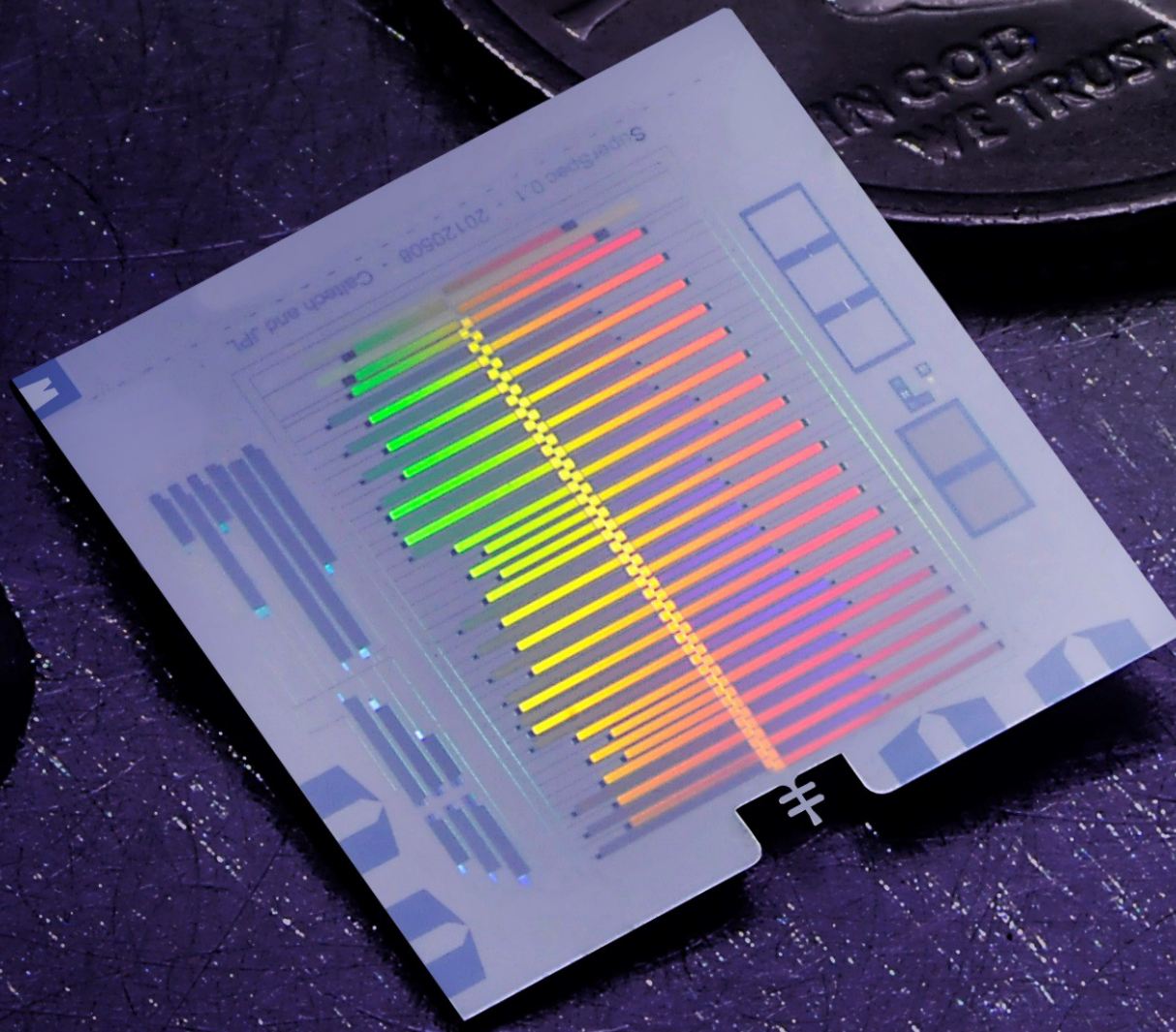


Probing the dark ages at mm-wavelength KIDs and on-chip spectrometers

Erik Shirokoff, U. Chicago

ANL Workshop on Innovative Devices and Systems





The SuperSpec Team

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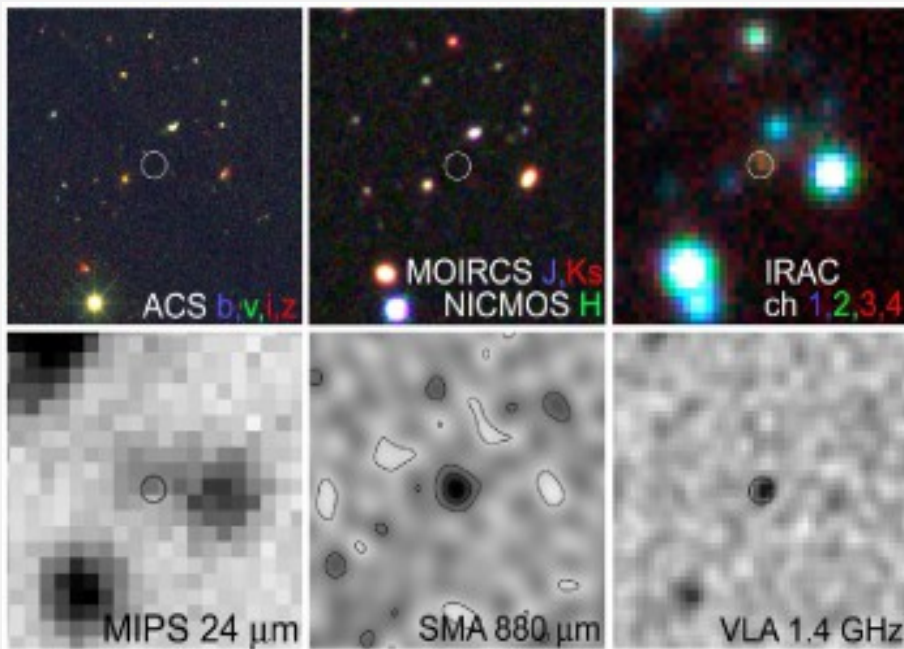
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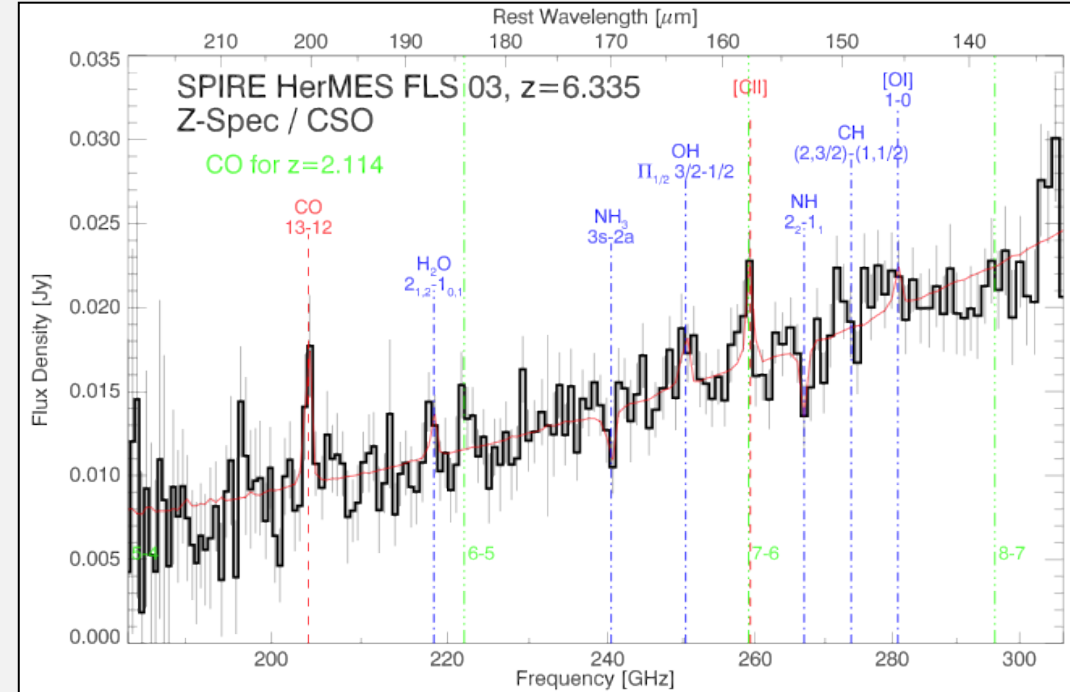


Spectroscopic redshift surveys

- Current and near-future continuum imaging surveys will rapidly discover new populations of Sub-Millimeter Galaxies
- Redshift determination & studies of interstellar medium require spectroscopy of CO, [CII] and other fine-structure lines at mm-wavelength
- A 3 year survey with a 30 – 300 beam instrument such as X-Spec will measure redshifts for thousands of galaxies at $z > 3.5$



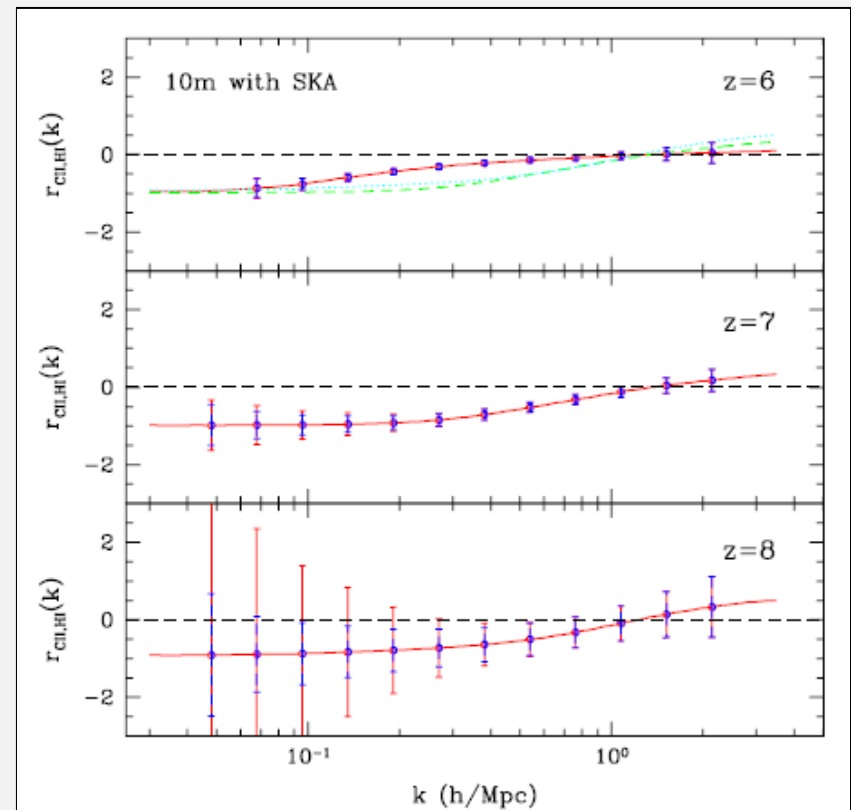
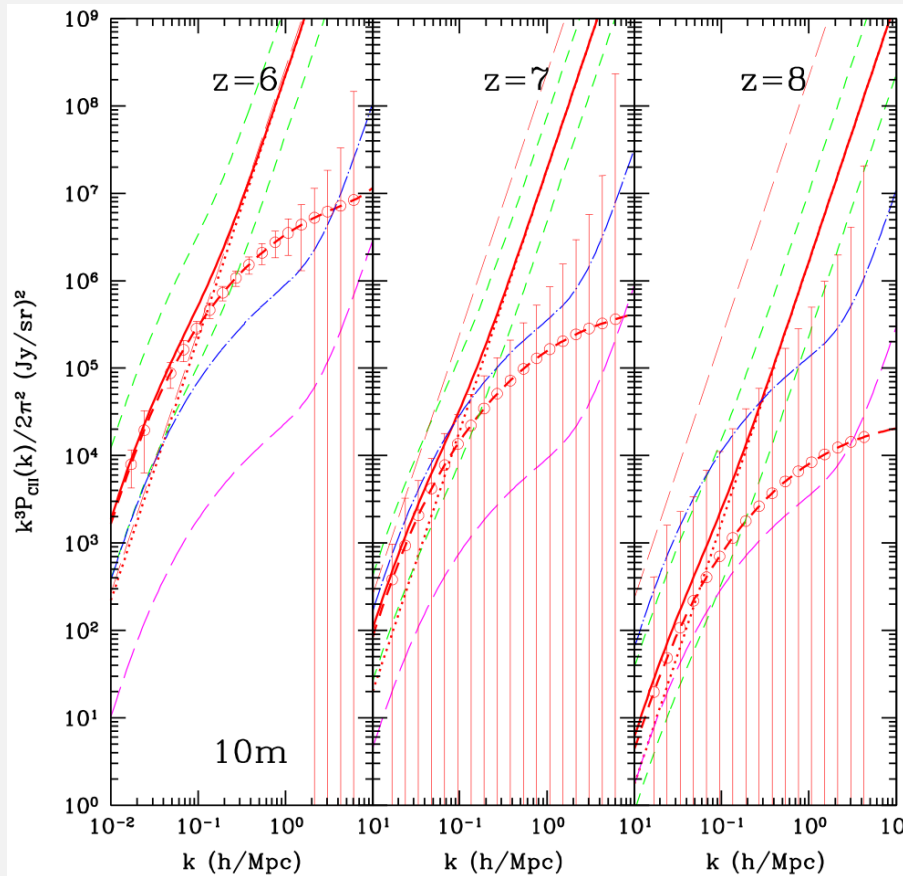
GOODS 850-5; Wang+09



Riechers+13

Tomographic Mapping of [CII] at EoR

- Line intensity mapping of [CII] 158 μm during reionization probes
 - Galaxy clustering
 - Mean [CII] intensity and galaxy luminosity function
- Optimum resolving power is $R \sim 100$



Z-Spec: a pioneering mm-wavelength spectrometer

120 channels from 190-305 GHz $R = \frac{\nu_{\text{obs}}}{\Delta\nu} \approx 250$

First light in 2005, and still in the field producing science results.

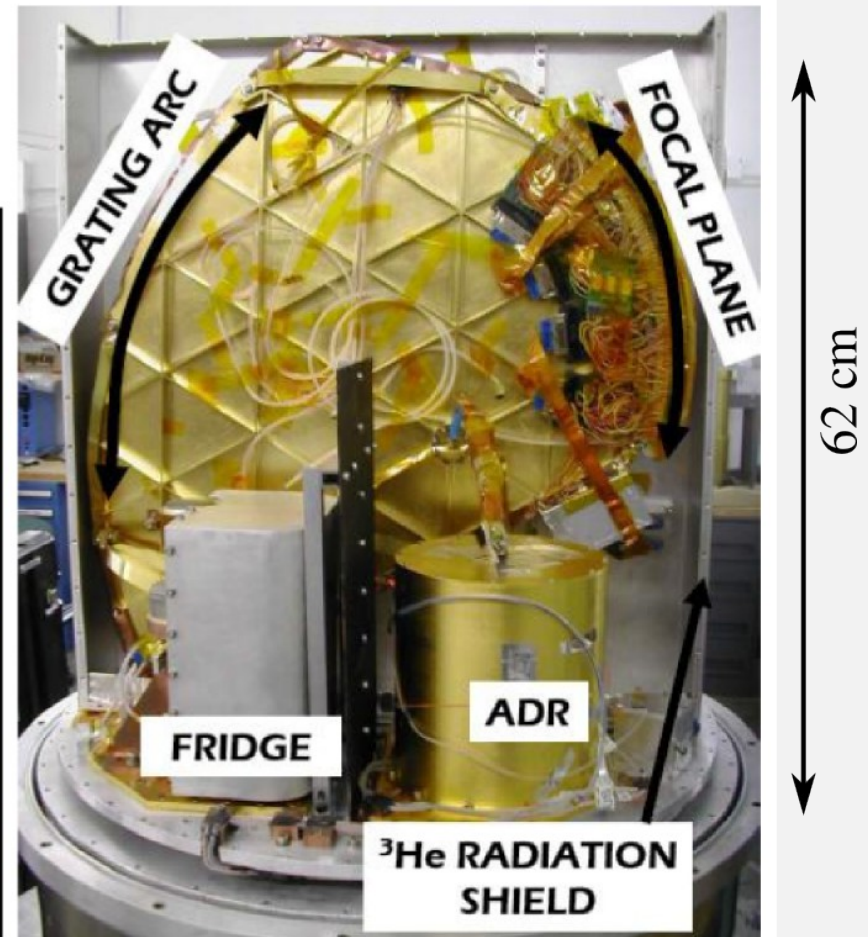
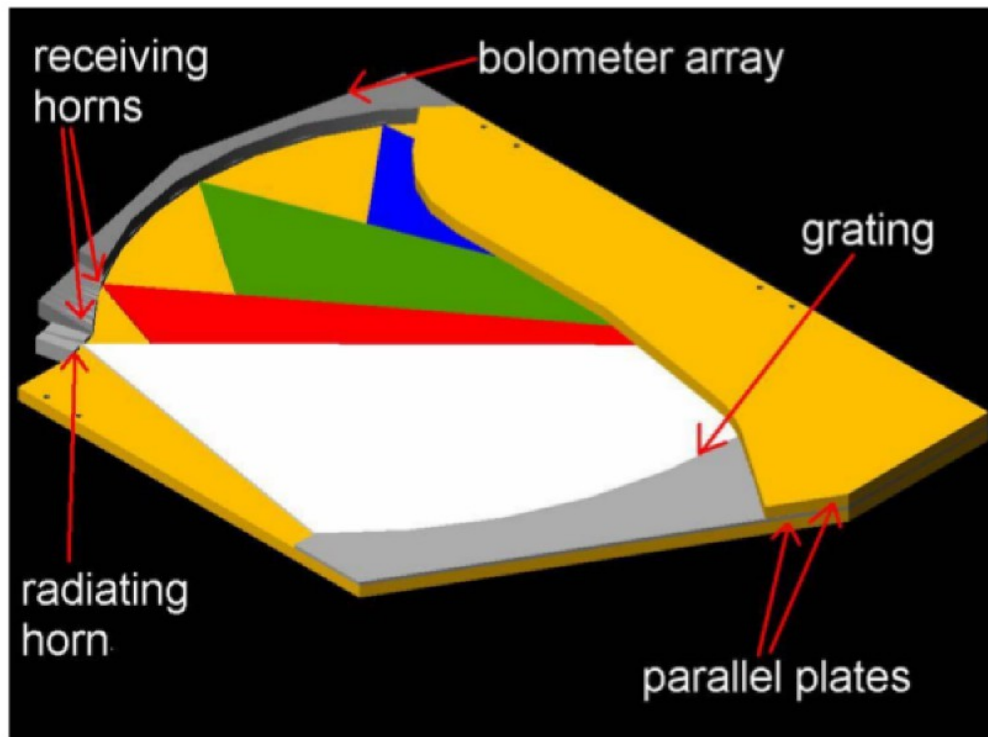


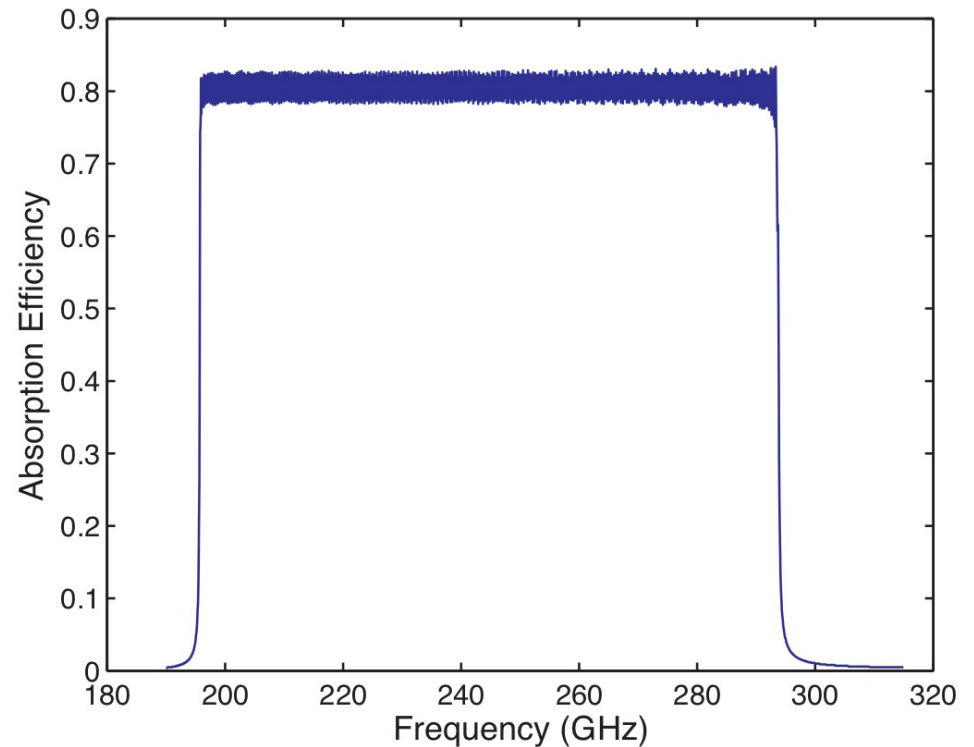
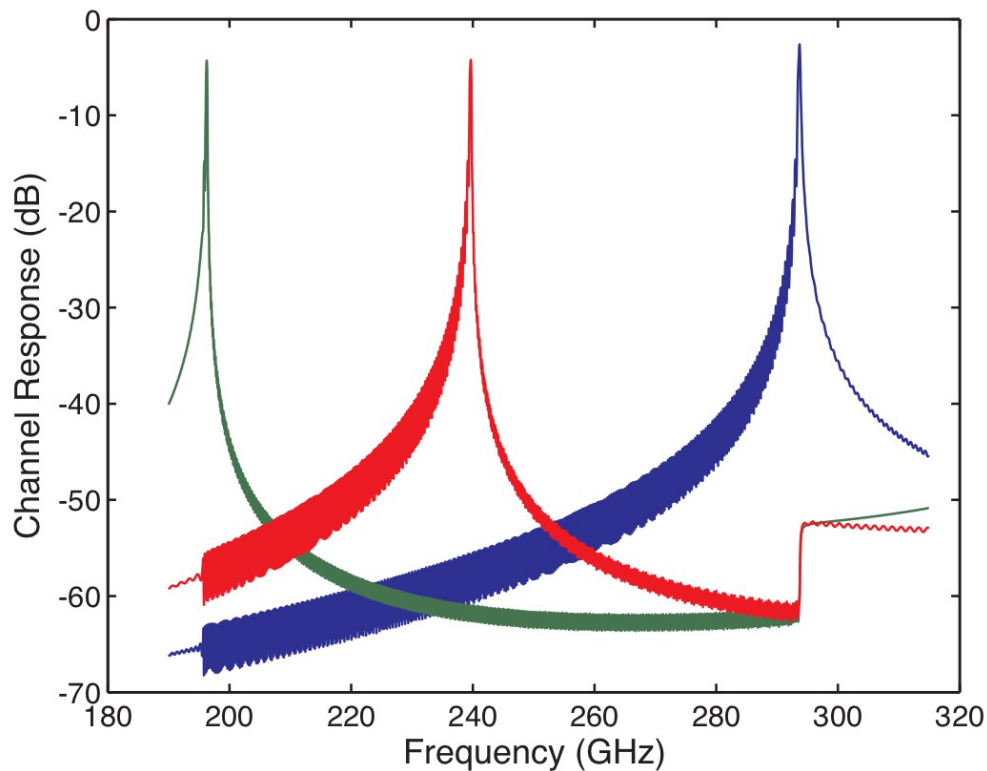
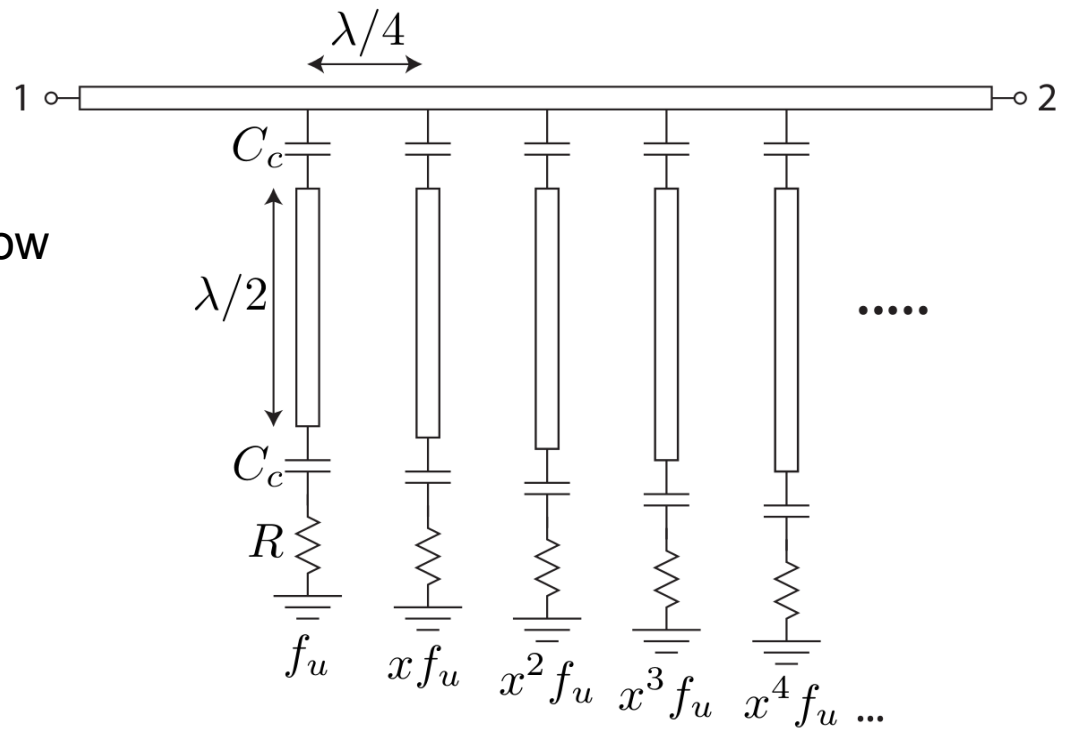
Image: Earle 2006

A general filter bank
(or cochlear) spectrometer:

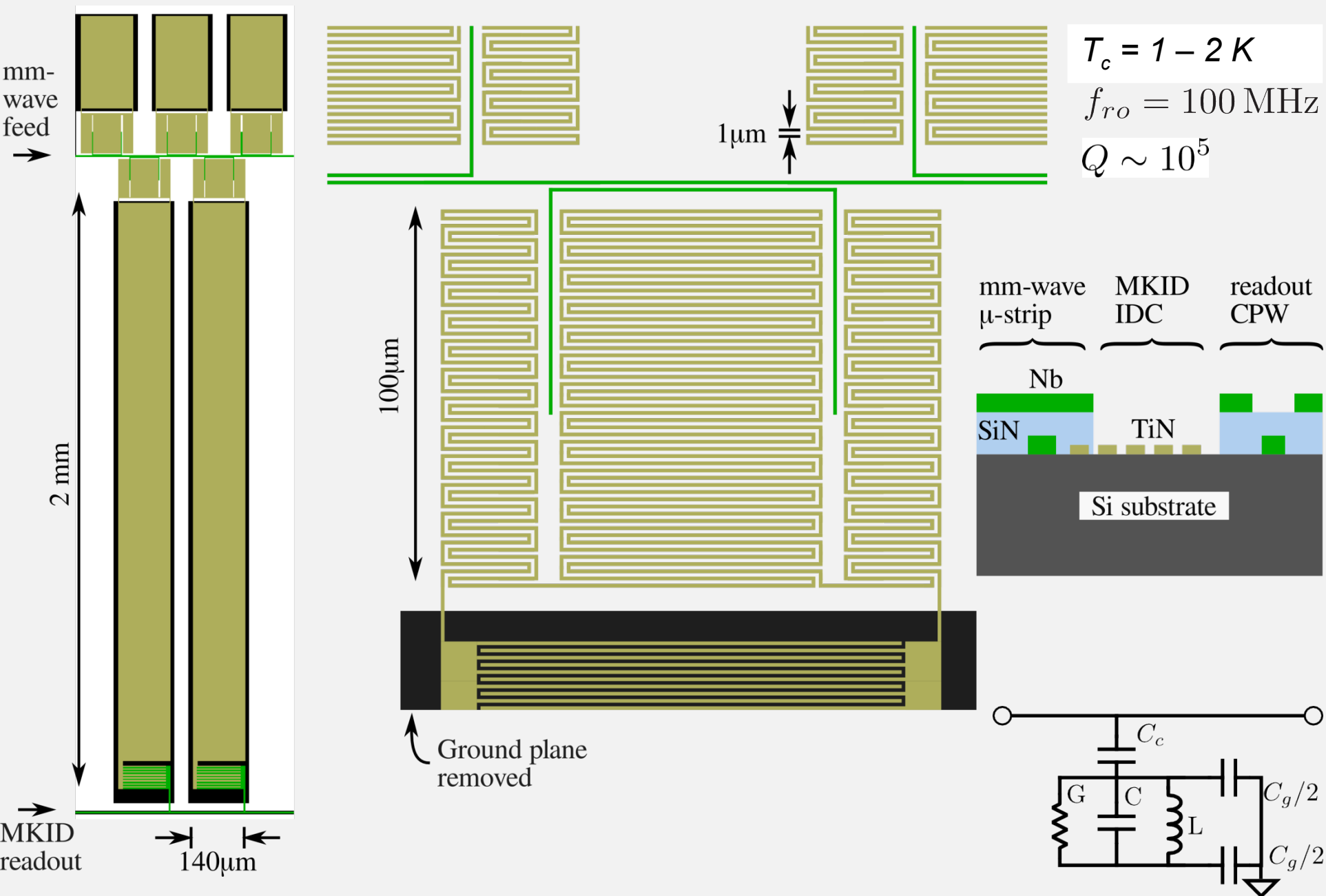
Incoming radiation is sorted by narrow band filters

Each channel couples to a power detector

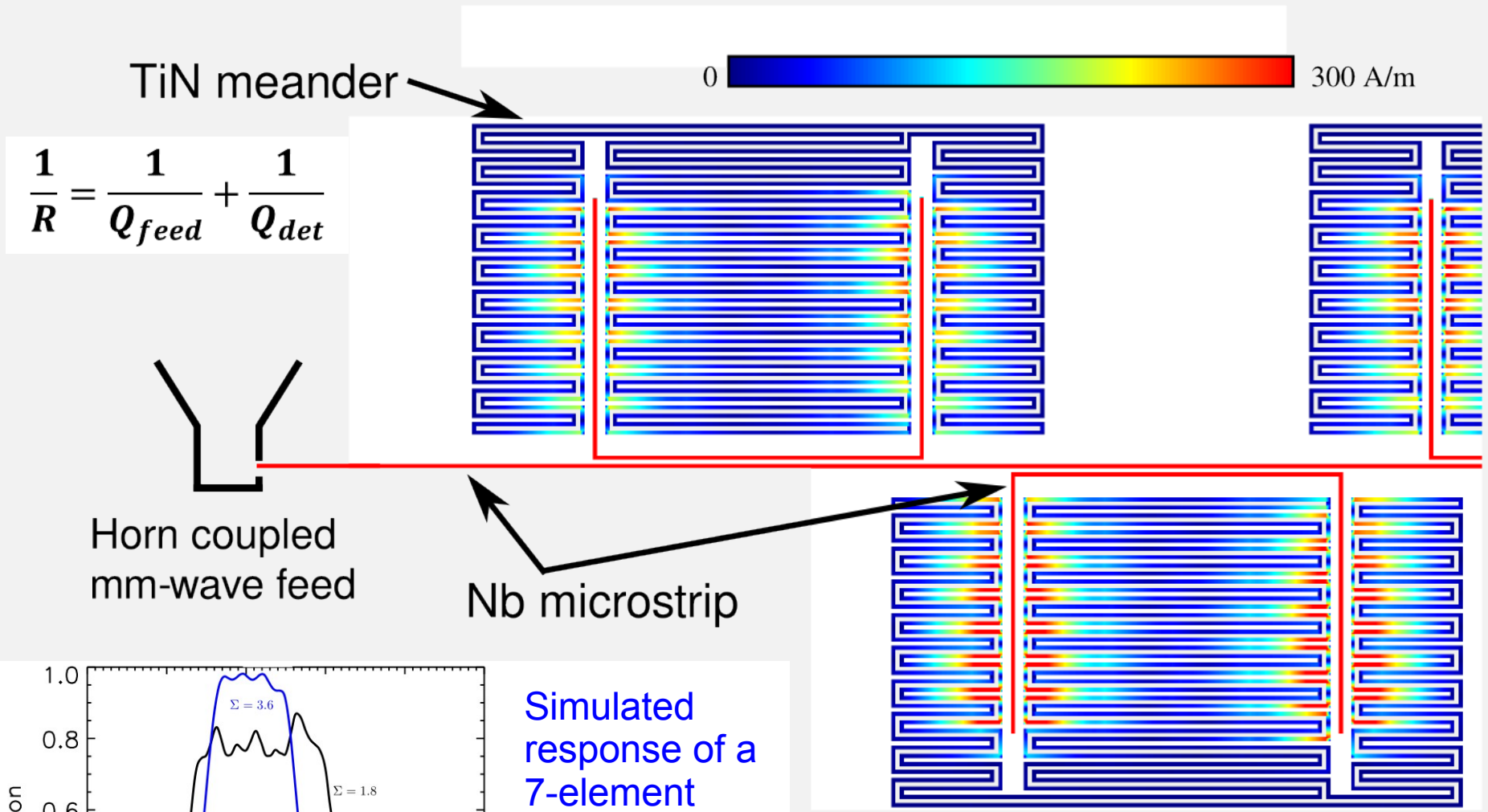
Channel width and spacing are independently adjustable



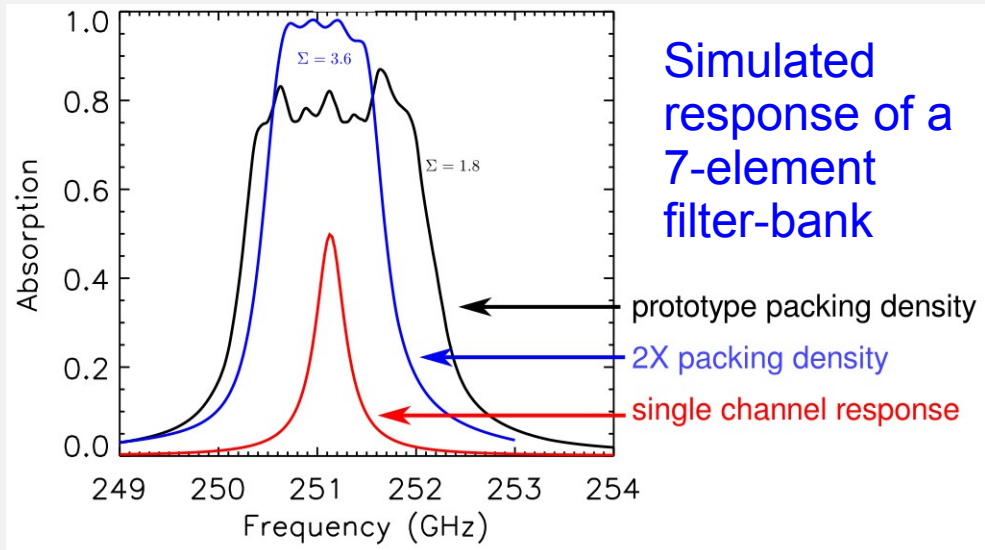
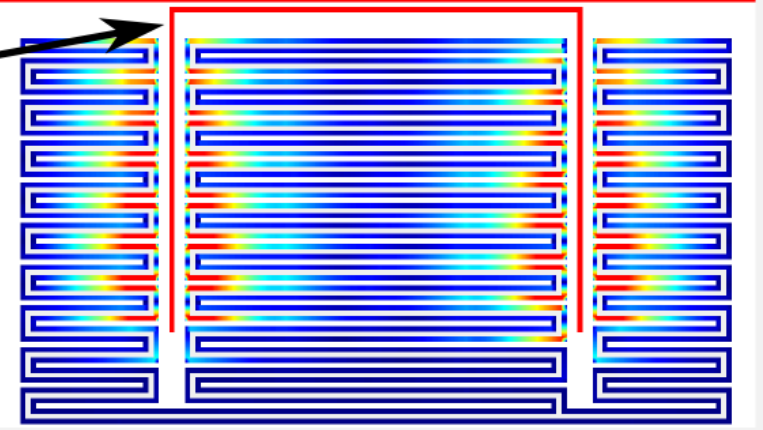
SuperSpec first generation design



Sonnet Simulations



$$\frac{1}{R} = \frac{1}{Q_{feed}} + \frac{1}{Q_{det}}$$

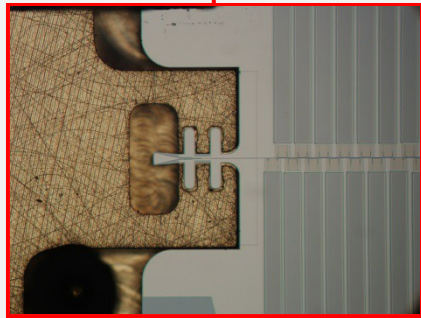


Gen1 Chip

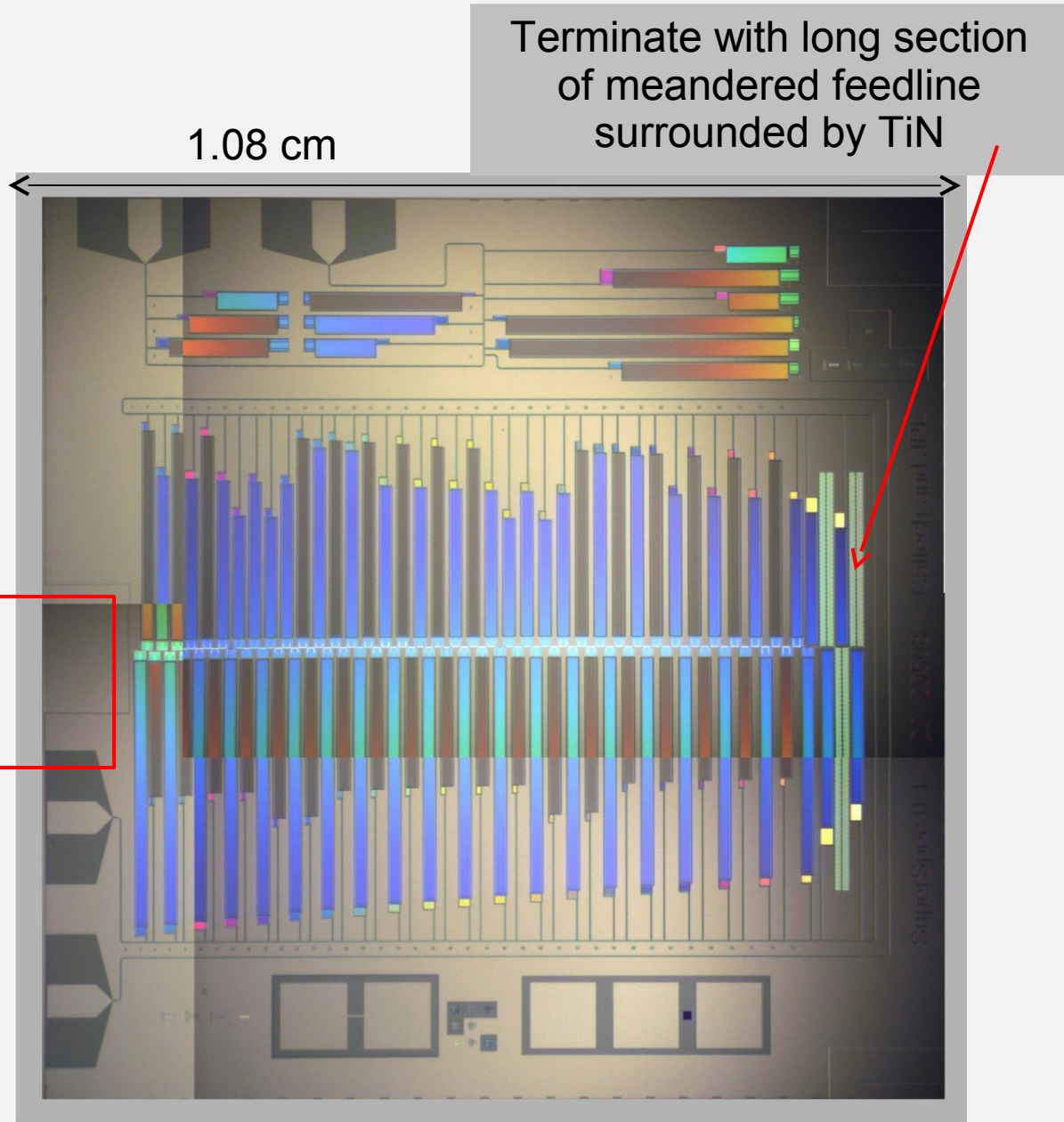
73 spectral channels
- $f_0 = 200 - 300$ GHz
- $Q = 300 - 1400$

8 broad-band absorbers

~95% optically active



probe-fed waveguide on
25 μm SOI device layer

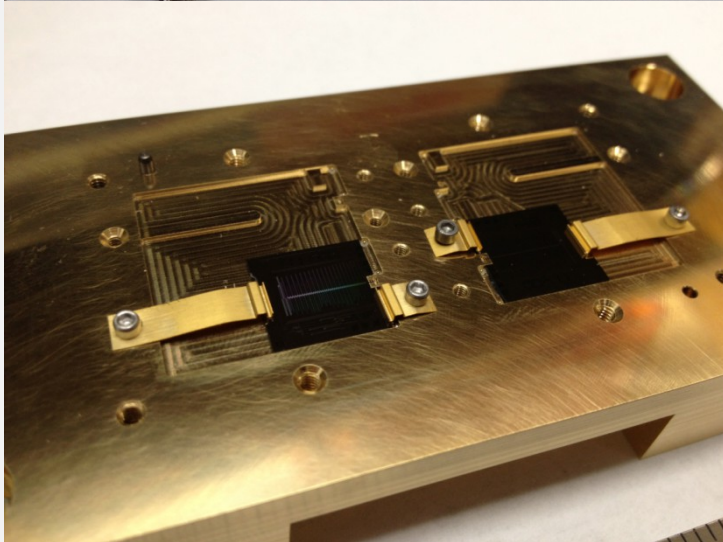
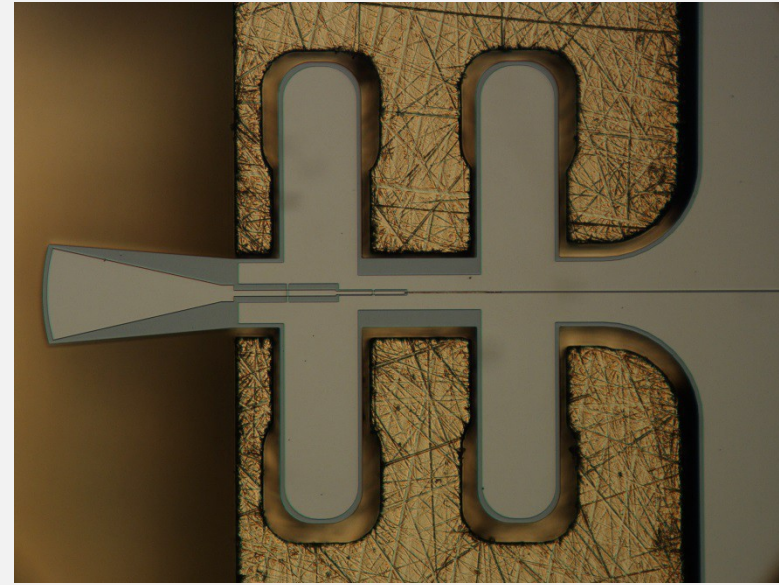
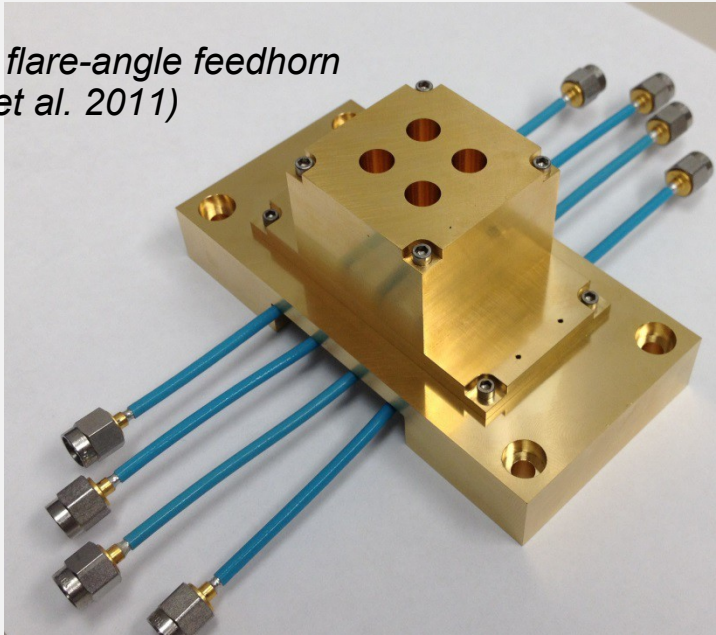


Terminate with long section
of meandered feedline
surrounded by TiN

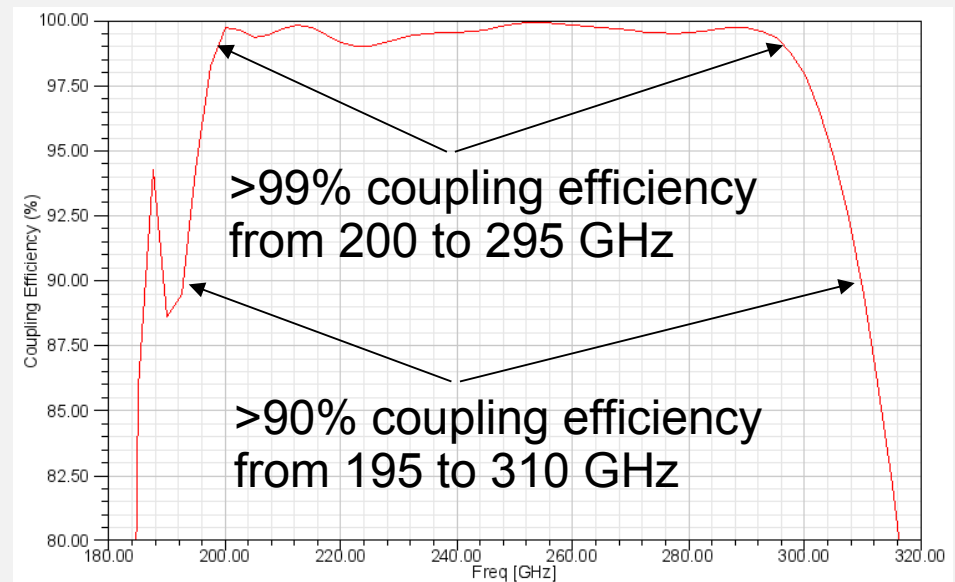
1.08 cm

Gen1 Probe-Fed Waveguide and Horn

*Multiple flare-angle feedhorn
(Leech et al. 2011)*

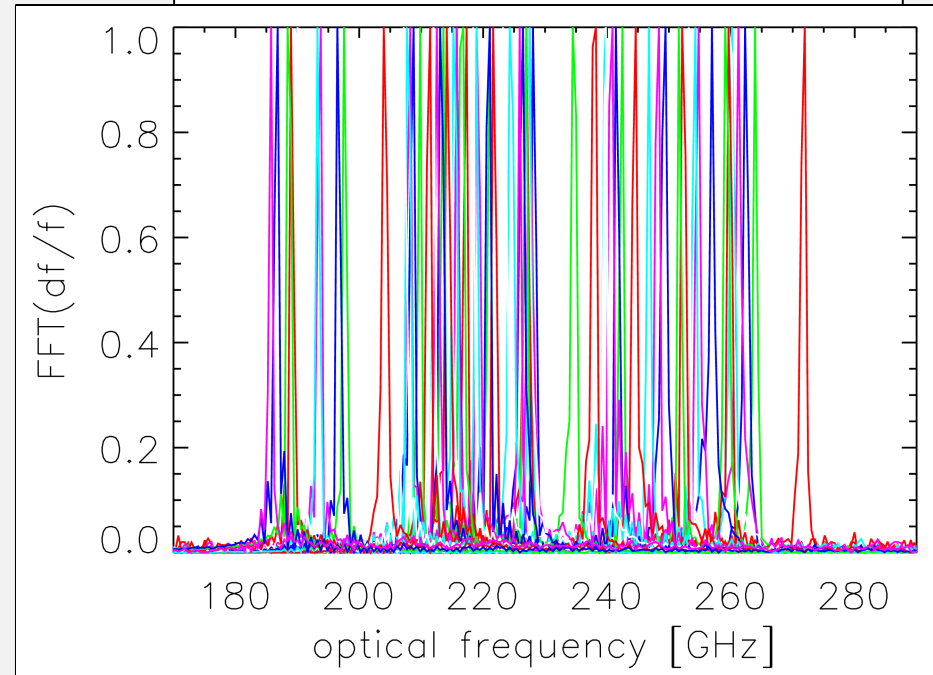
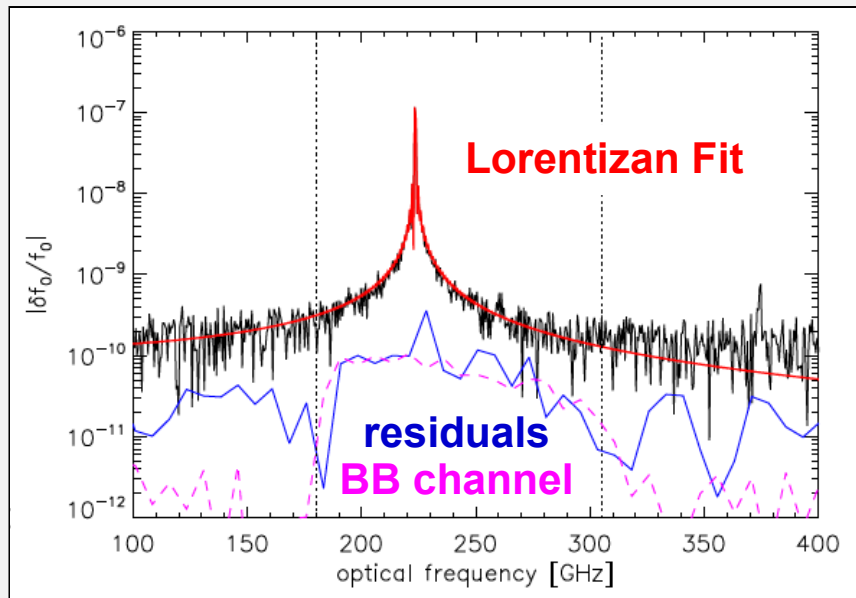


Design and images by T. Reck



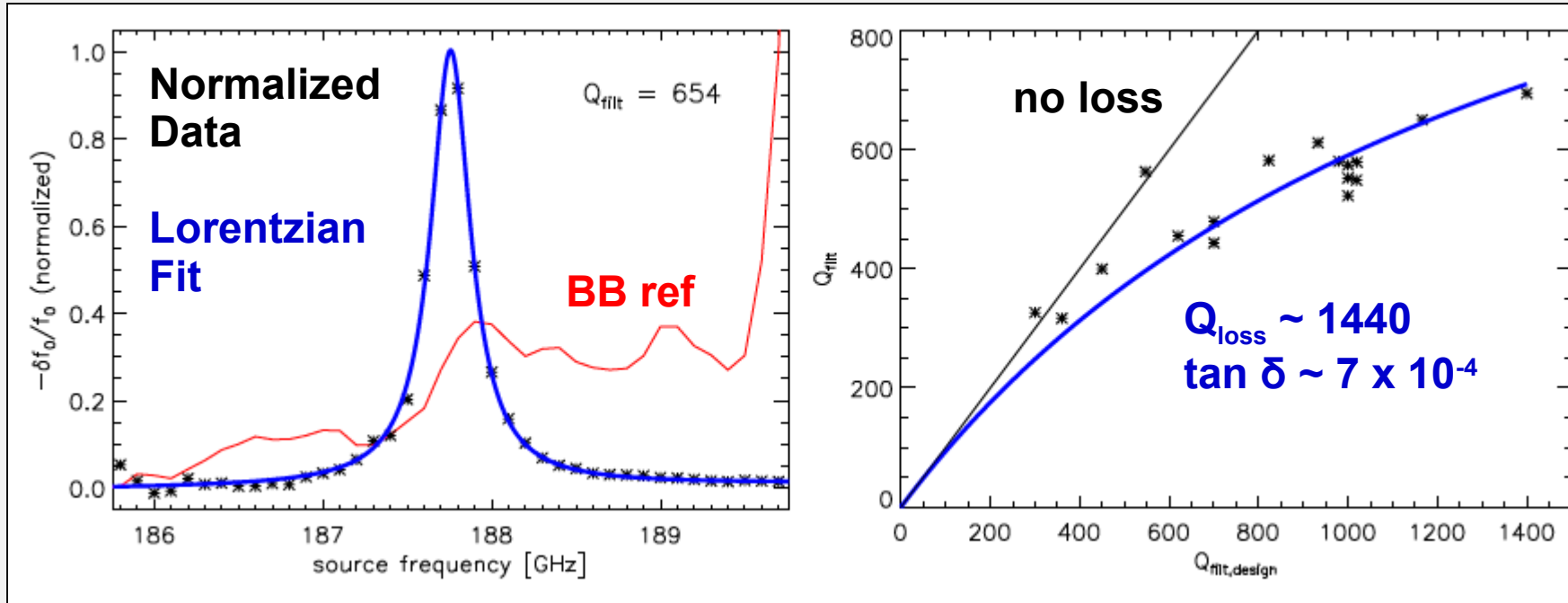
FTS Measurements

Normalized profiles of 71 spectral channels readout in parallel



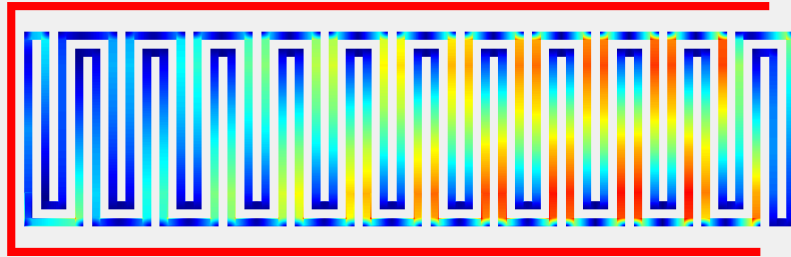
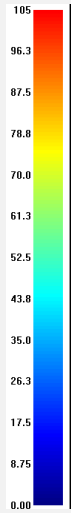
- Full band spectra measured with CASPER-ROACH based FPGA readout system (same system deployed by MAKO/CSO)
- Residual out of band response typically 30dB below peak
- Channel center placement has 2 - 3% scatter - partially systematic with frequency, Q, location in filter bank
- Too large to be errors in resonator length --> wavespeed variation
- Will soon test chips with large bank of near-identical channels to measure real dispersion.

Coherent Source Measurements



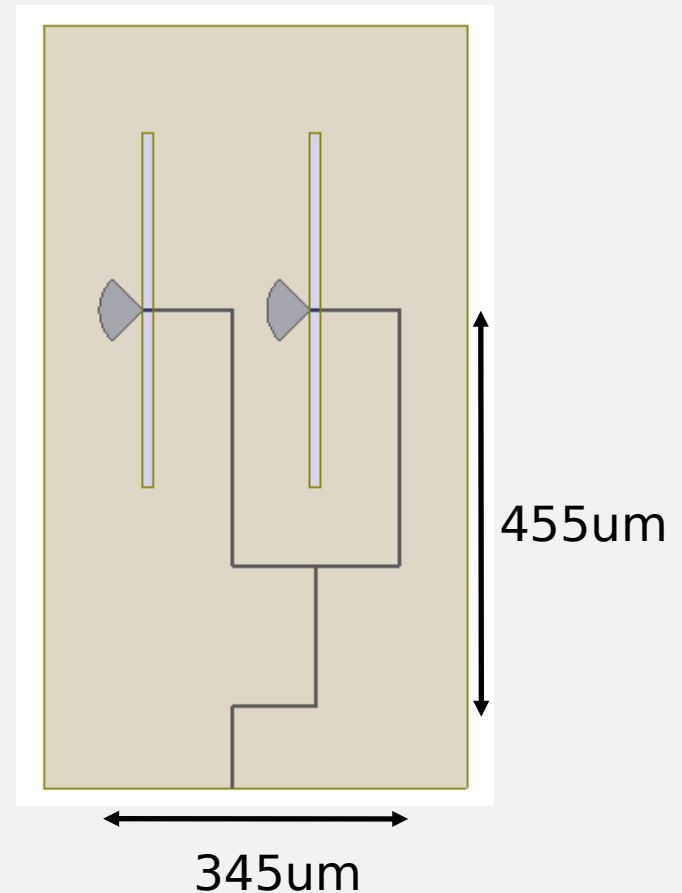
- Spectral response characterized using a swept coherent source
- Normalize response with near simultaneous measurements of BB ref channel - well described by Lorentzian
- Comparison of designed and measured Q indicates a source of loss characterized by $Q_{\text{loss}} \sim 1440$ --> likely SiN_x ILD in microstrip
- **Greater than 50% of the incident power lost for $R > 420$**
- Better dielectrics (a-Si, crystal Si)

Gen2 - Improved NEP and diagnostics

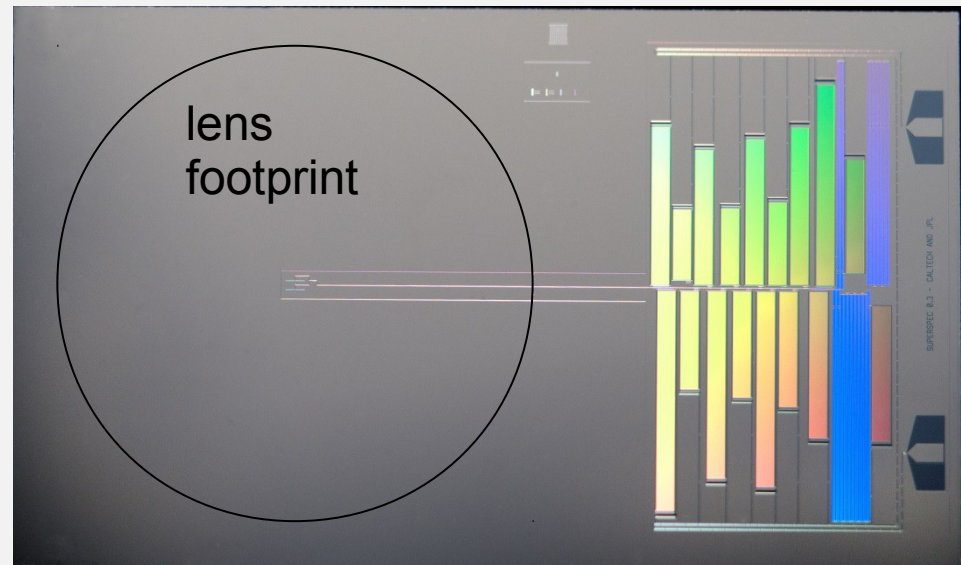
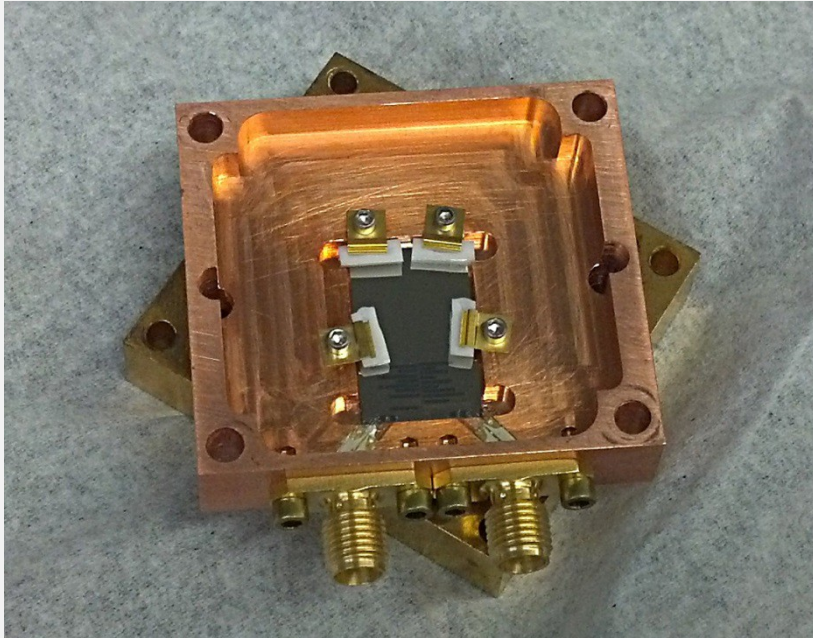
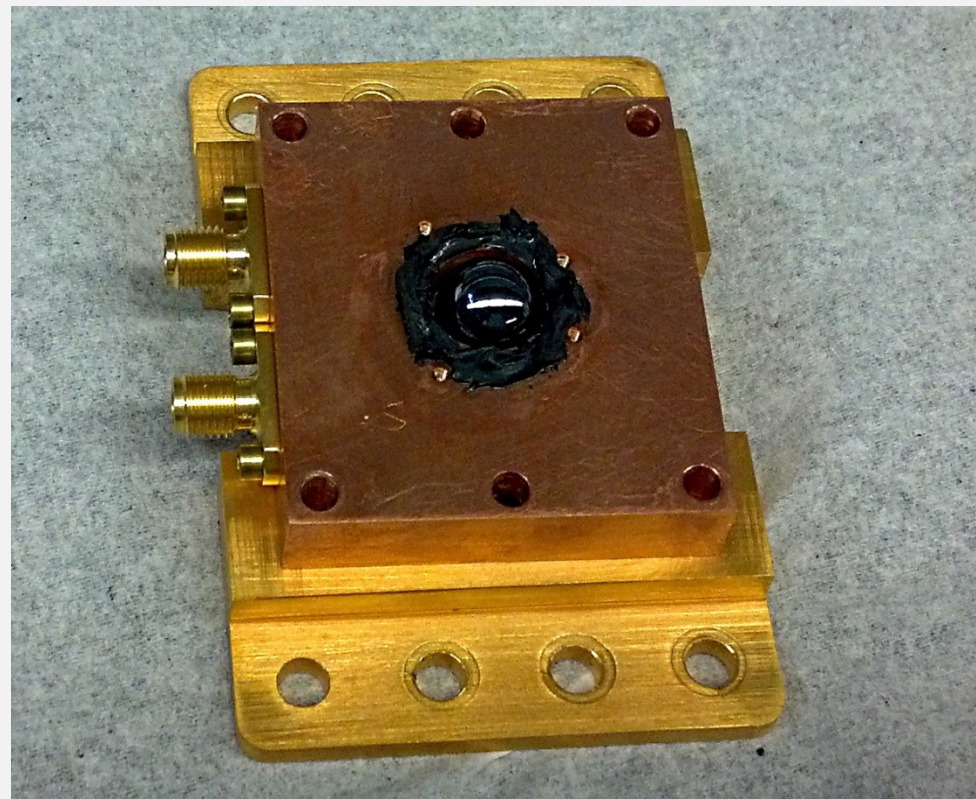
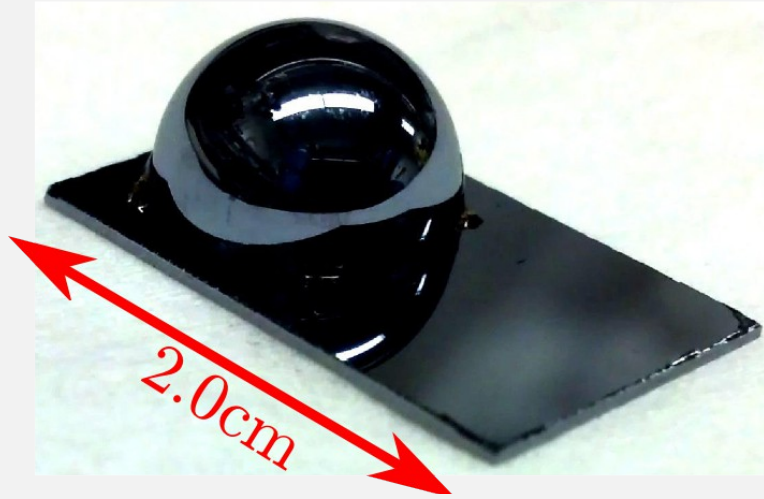


- Modifications to boost sensitivity
 - Shrink inductor volume by x5
 - More uniform current density
 - Wider IDC spacing

- Modifications to improve diagnostics
 - Simpler planar antenna + hyper-hemispherical lens
 - BB detectors couple to a longer section of the feedline, comparable to a wavelength in length
 - Small number (10) of isolated spectral channels
 - Dark channel

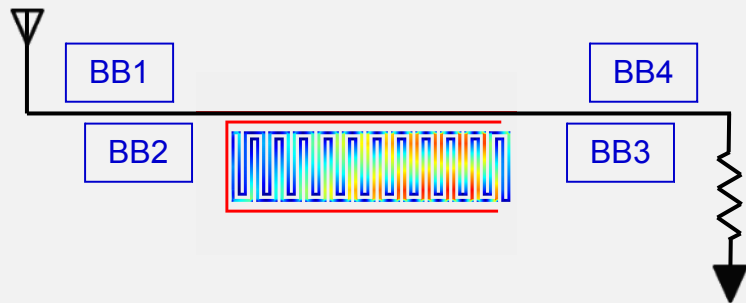


Gen2 Packaging



Socketout Measurement

BB channels – sections of meandered TiN in proximity to feedline, approx λ in length

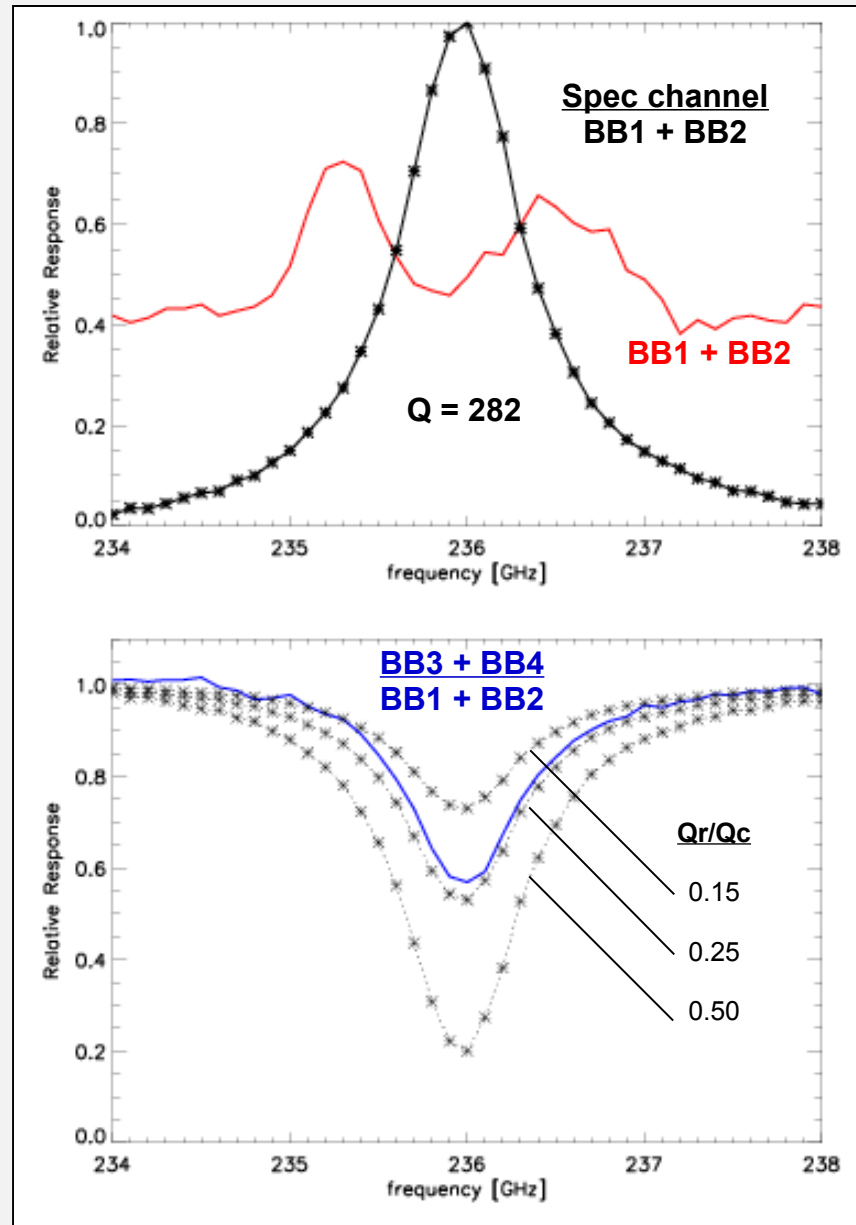


Modeling indicates

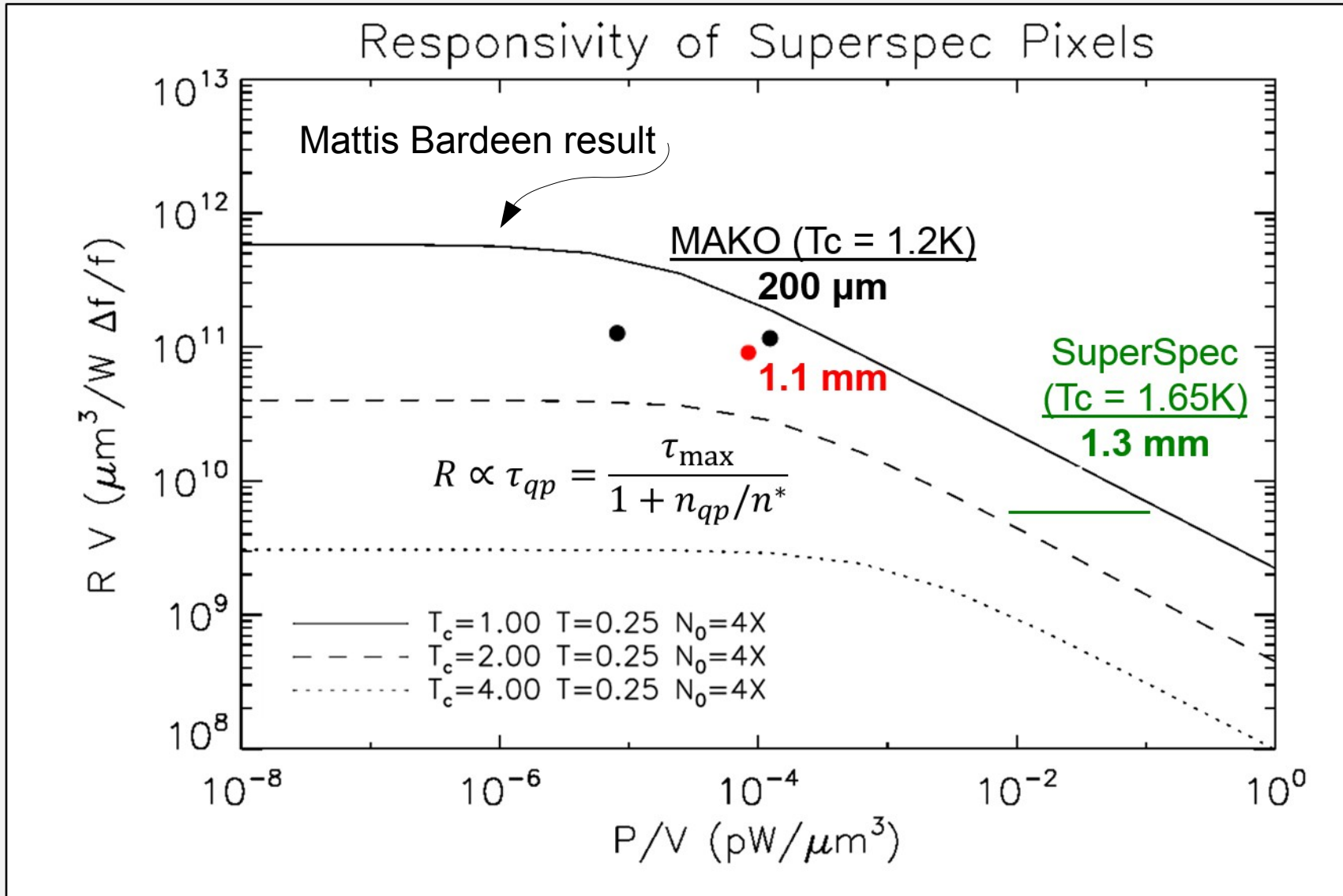
- $Q_r/Q_c \sim 0.25$
- Absorbed fraction $\sim 37\%$

With $Q_{loss} = 1440$

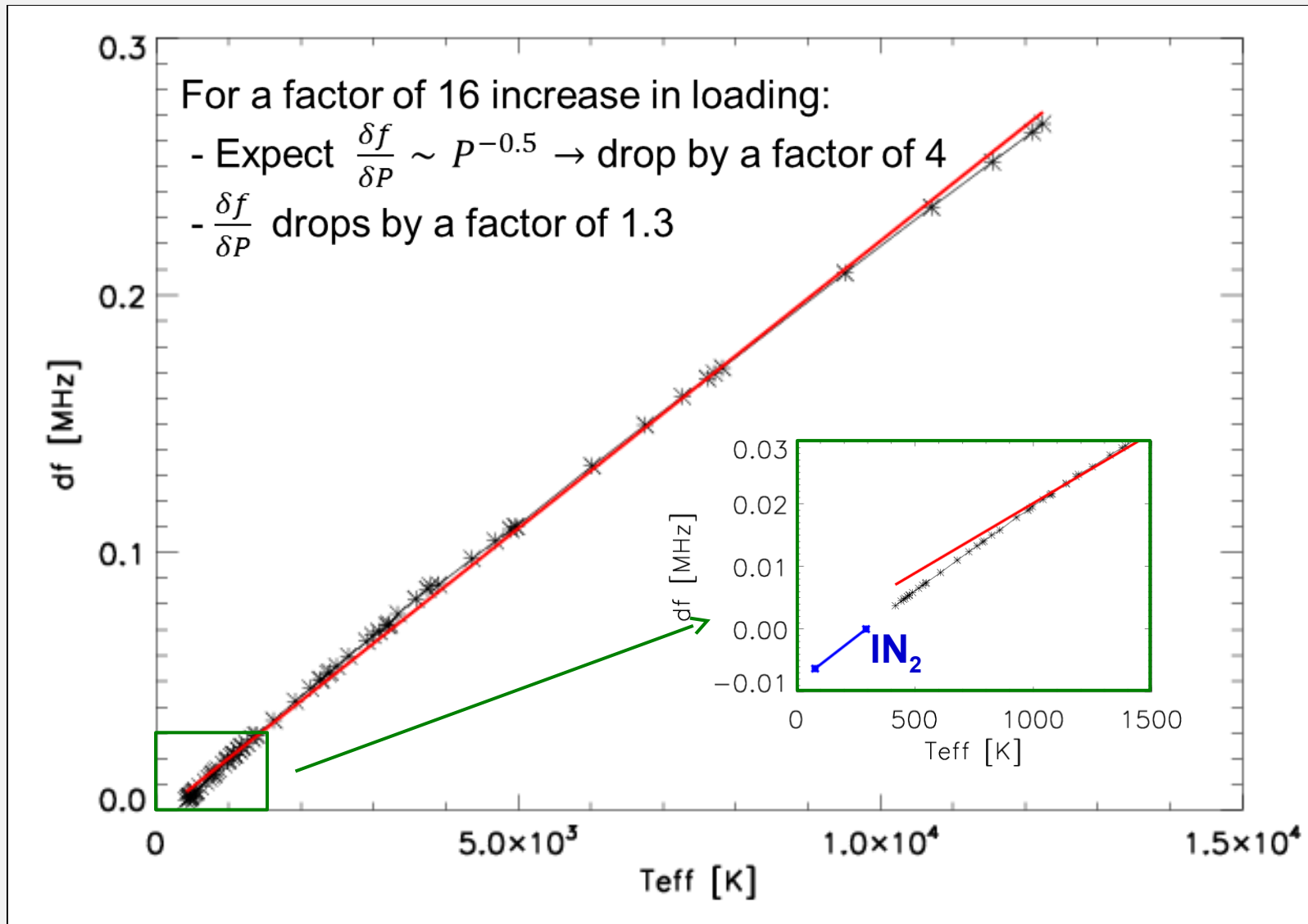
- **Detected fraction $\sim 28\%$**
- **Can achieve $\sim 34\%$ with $R = 250$, adjusted dimensions**



RV vs P/V plot

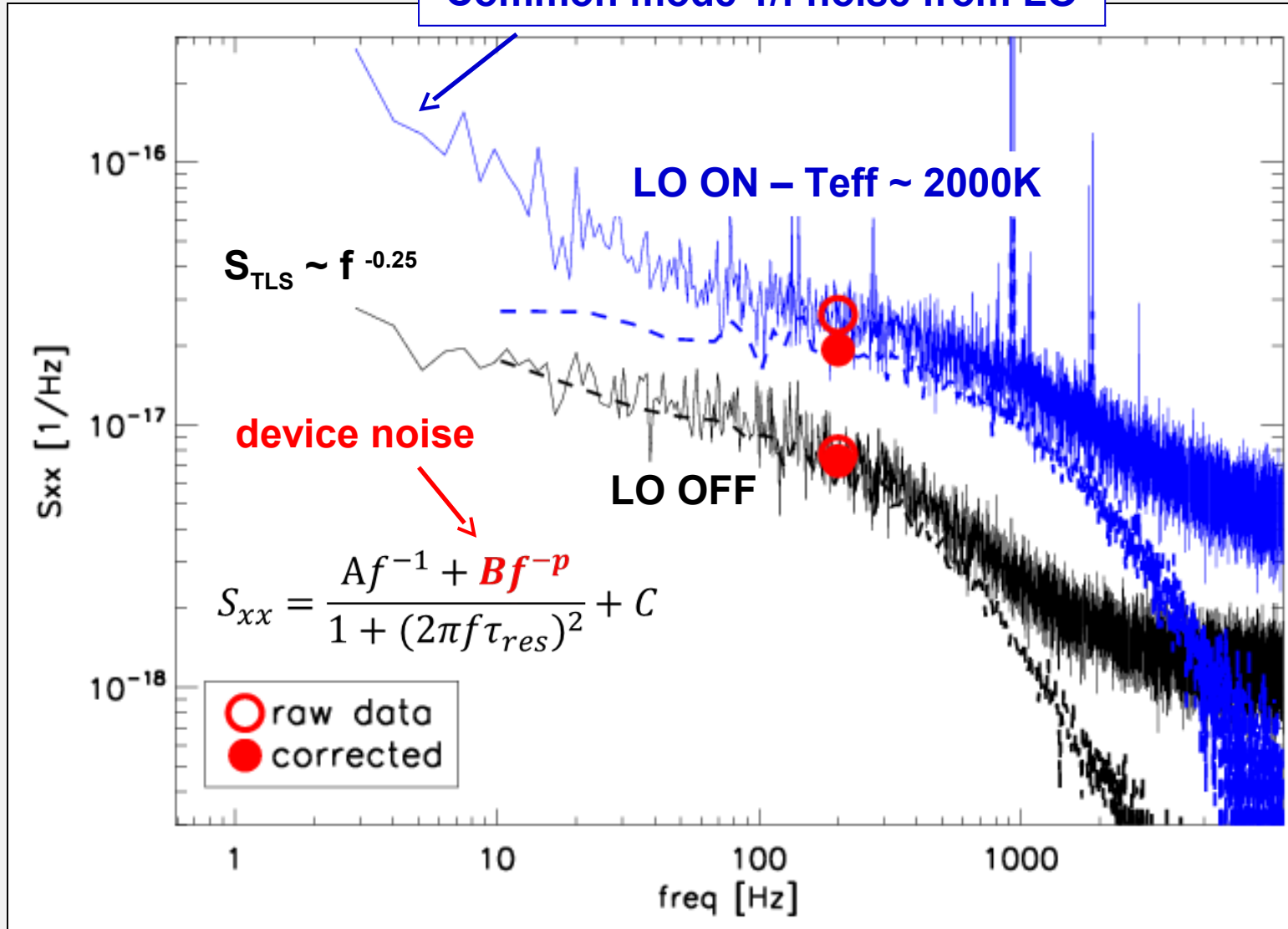


Close to linear frequency shift with loading

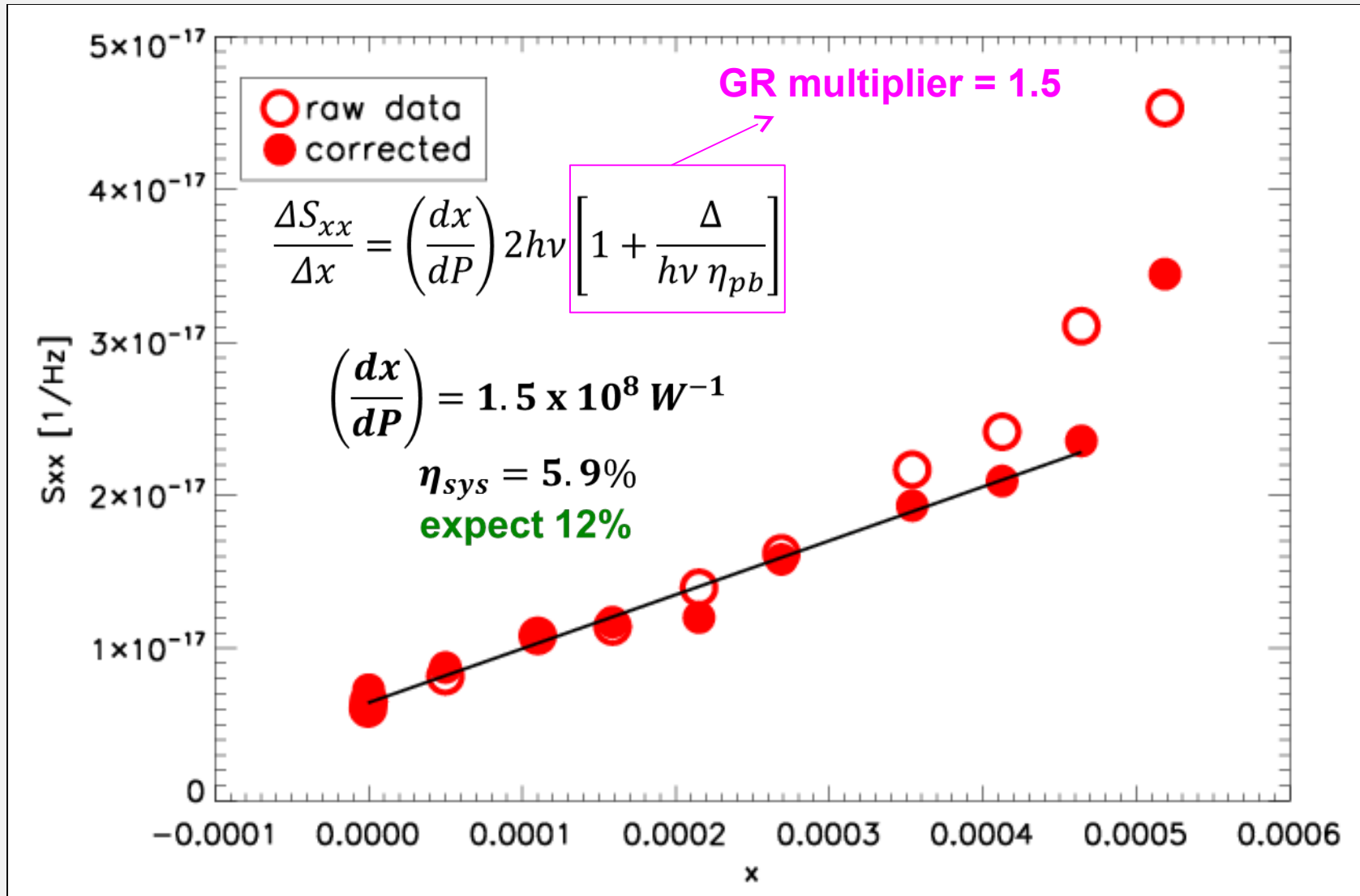


Excess Noise with Loading

Common mode 1/f noise from LO



Excess Noise with Loading



System NEP and Future Improvements

- Our current $R = 250$ channels provided $NEP_{\text{TLS}}(1\text{Hz}) = 5.2 \times 10^{-16} \text{ W/Hz}^{1/2}$, front of cryostat -> **factor of 16 above NEP γ at CSO**
 - Near term improvements -> **factor of 3.4 increase**
 - AR coating lens
 - Adjusting spectrometer coupling strength
 - Dropping T_c from 1.65K to 1.2K
- > **factor of 2 better than NEP γ for $R = 50$!**
-> **candidate for tomography**
- Moderate term improvements -> **factor of >6 increase**
 - Reducing inductor linewidth from $1\mu\text{m}$ to $0.5\mu\text{m}$
 - Anomalous factor of 2 in system optical efficiency
 - Thicker capacitor, wider IDC spacing
 - Longer term improvements
 - Switching to $T_c = 0.8\text{K}$ -> **factor of 2.5 increase**
 - Better dielectric -> **factor of 1.4 increase**

Summary

We've achieved:

- Working mm-wave filter bank
- Narrow ($R \sim 700$) channels
- Low out-of-band loading (1 part in 10^4)
- High-Q ($>10^5$), 100 MHz KIDs
- Background limited operation at $R \sim 50$
- Hundreds-of-pixel FPGA MUX readout

We're working on:

- New design for higher response
- Understanding TiN response
- Channel placement accuracy
- Lower loss dielectrics for high-R channels

Extra Slides Follow

Multiplexing requirements set minimum value of Q_i .

$$f_i = f_0 x^i + \delta_i \quad \sigma = \sqrt{\left\langle \frac{\delta_i}{f_i} \right\rangle}$$

$$\text{Collision} \equiv f_i - f_j \leq 5Q_i f_i$$

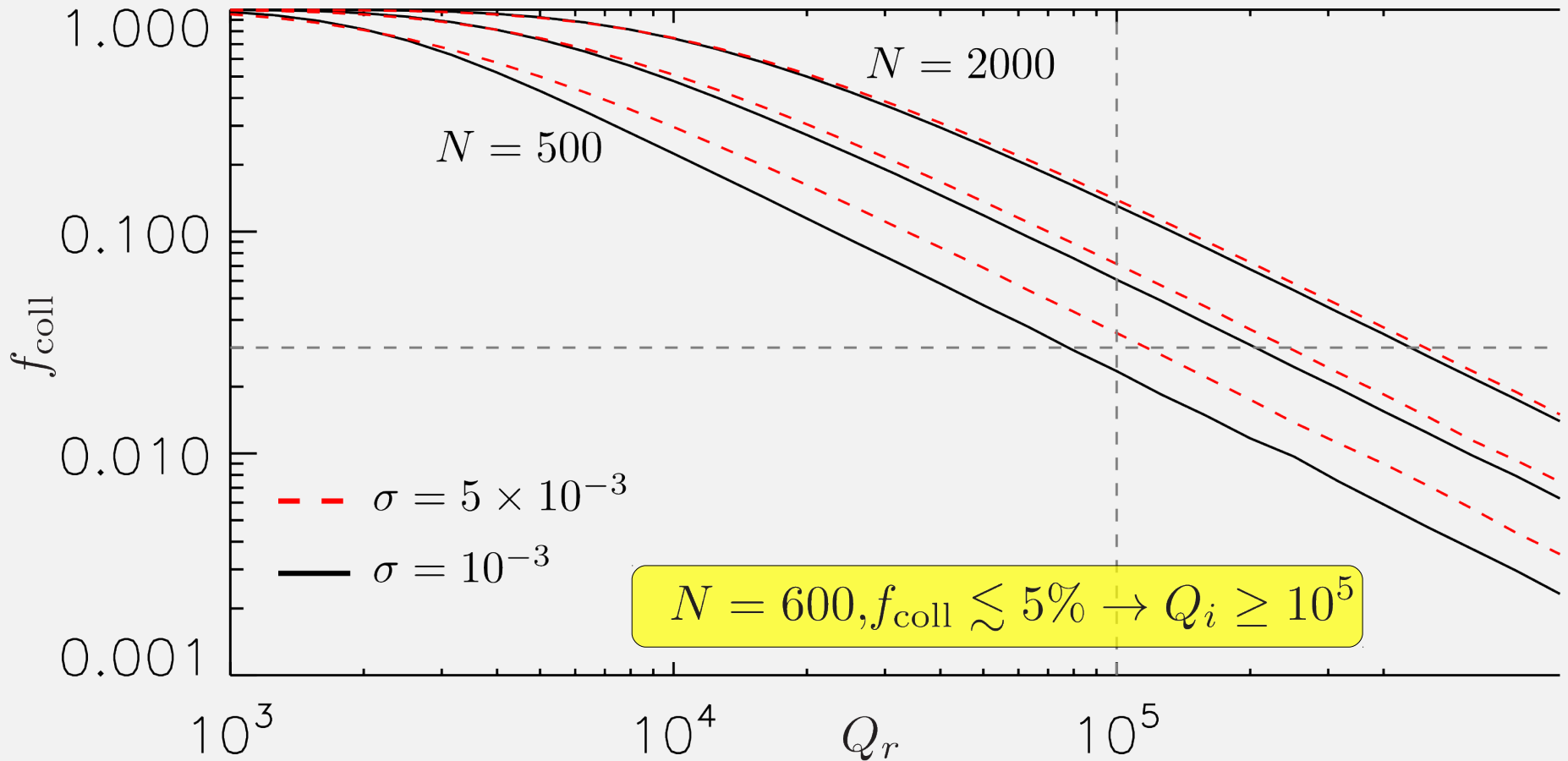
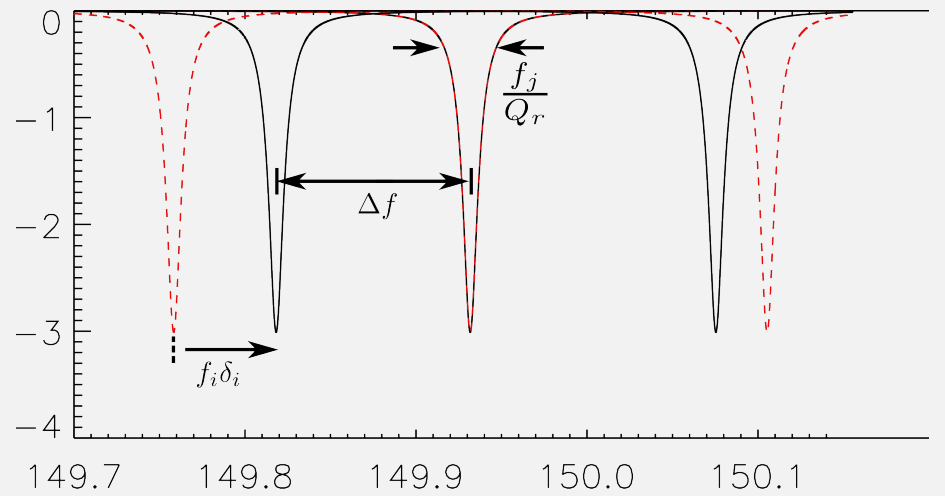
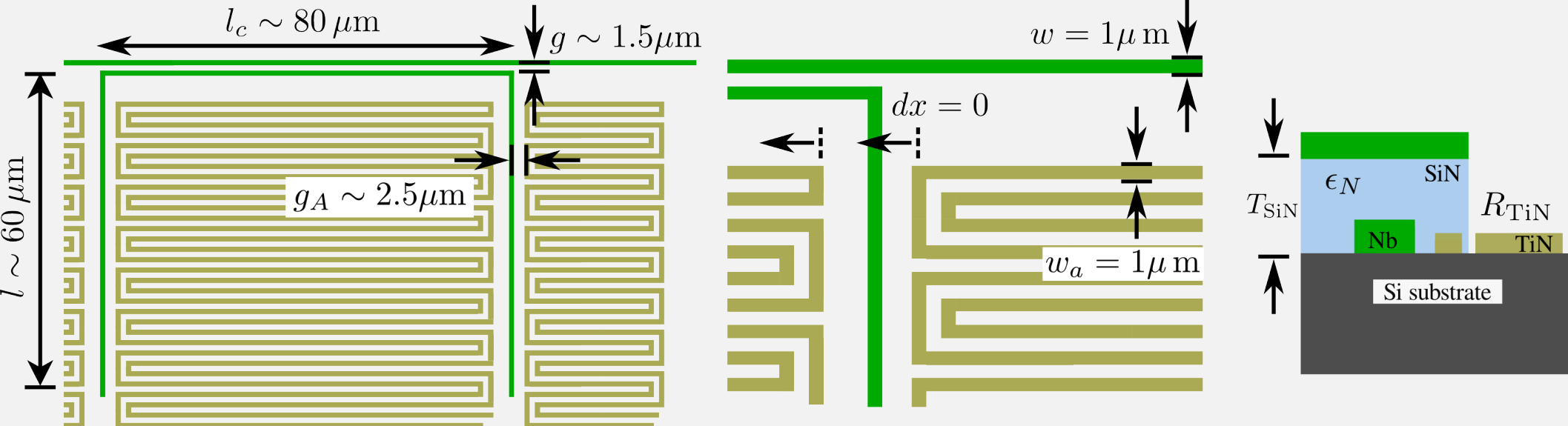


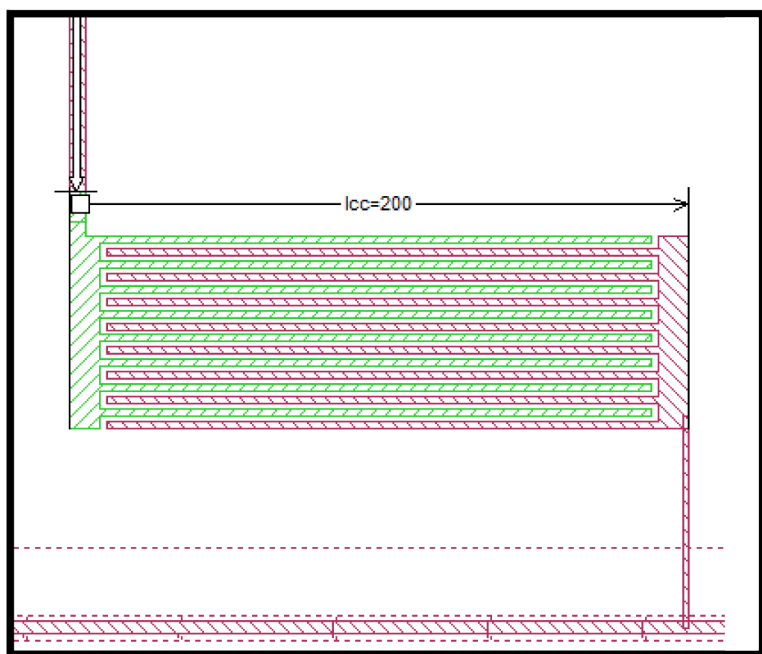
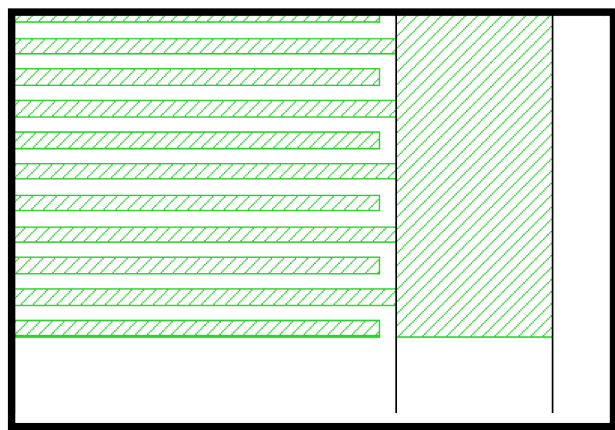
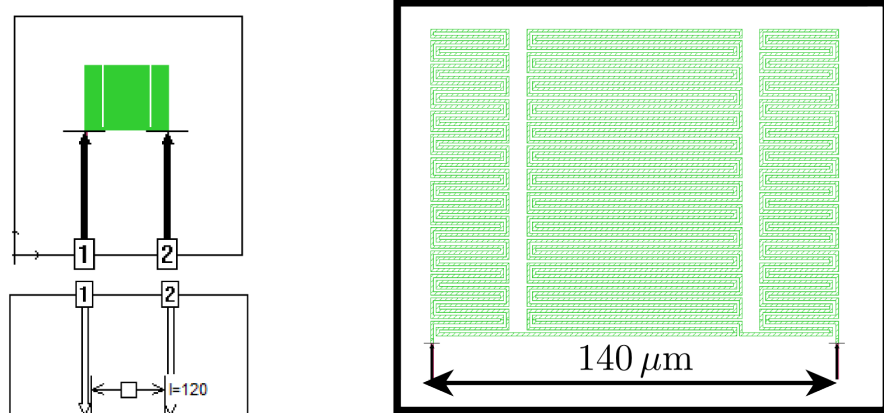
Figure based on Zmuidzinas internal memo



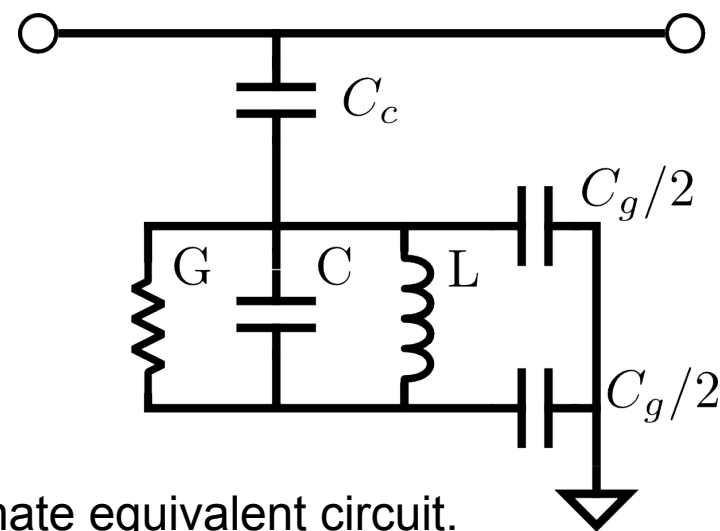
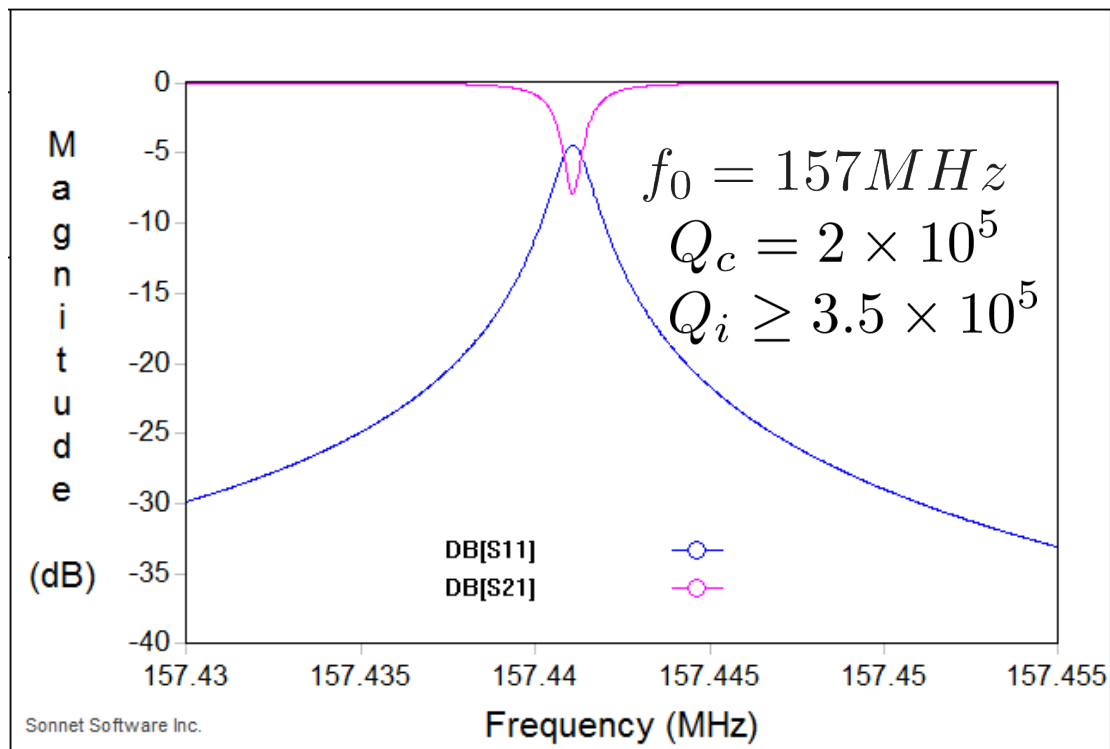
Tolerances for an $R = 700$ μ -strip resonator on 0.5μ silicon nitride

	variable	description	change	Fractional change in			
				Freq	Q_i	Q_c	Q_r
Lithography	l	resonator length	$0.1 \mu\text{m}$	1×10^{-3}	–	–	–
	g	feed to reso gap	$0.1 \mu\text{m}$	8×10^{-5}	–	0.19	0.09
	g_A	absorber to reso gap	$0.1 \mu\text{m}$	4×10^{-5}	0.05	–	0.03
	w	Nb line width	$0.1 \mu\text{m}$	3×10^{-3}	0.06	0.11	0.08
	w_A	TiN line width	$0.1 \mu\text{m}$	6×10^{-5}	0.06	–	0.03
	dx	Nb/TiN offset in x	$0.1 \mu\text{m}$	5×10^{-6}	0.006	–	0.003
Materials	R_{TiN}	Resistivity	20%	6×10^{-5}	0.03	–	0.02
	ϵ_N	SiN permittivity	10%	0.03	0.20	-0.03	0.09
	T_N	SiN Thickness	10%	2×10^{-3}	0.30	0.40	0.35
	$\tan - \delta$	SiN loss	$+10^{-4}$	–	0.04	–	0.02

$$\left. \begin{array}{l} \text{Lithography} \\ \text{Materials} \end{array} \right\} \frac{\Delta Q_r}{Q_r} \sim 10\%$$

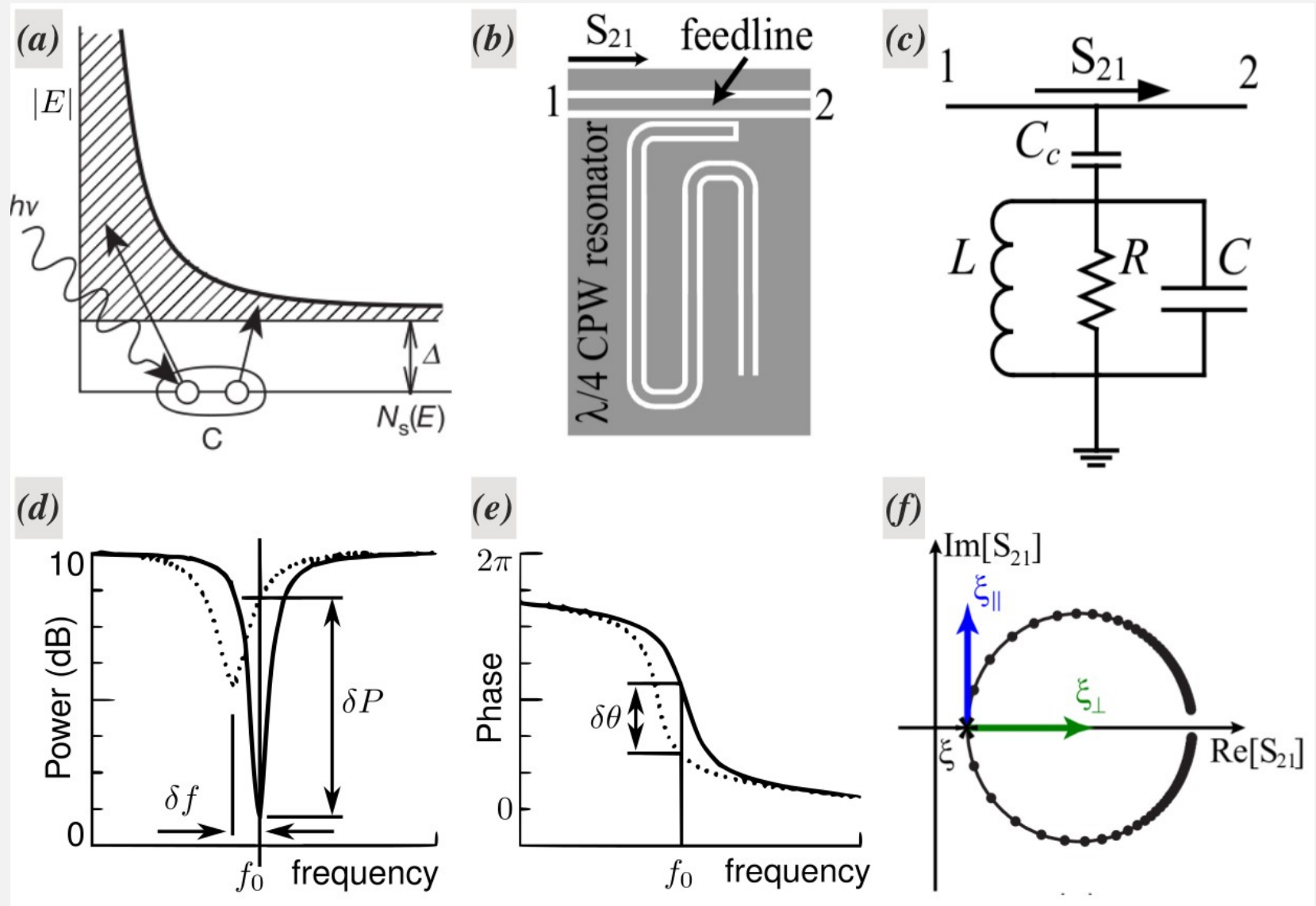


Sonnet simulation of a single MKID resonator



Approximate equivalent circuit.

We can use this as a radiation detector.



Figures from Mazin 2009 and Gao 2010